BD159G

Plastic Medium-Power Silicon NPN Transistor

This device is designed for power output stages for television, radio, phonograph and other consumer product applications.

Features

- Suitable for Transformerless, Line−Operated Equipment
- High Power Dissipation Rating for High Reliability
- These Devices are Pb−Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	350	Vdc
Collector−Base Voltage	V_{CB}	375	Vdc
Emitter−Base Voltage	V_{EB}	5.0	Vdc
Collector Current − Continuous	I_C	0.5	Adc
Collector Current − Peak	I_{CM}	1.0	Adc
Base Current	I_B	0.25	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 20 0.16	 W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

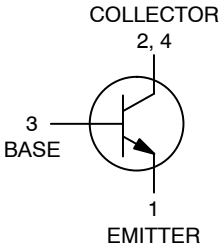
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	6.25	°C/W

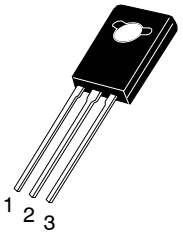
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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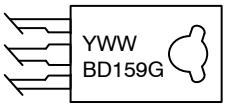
0.5 AMPERE
POWER TRANSISTOR
NPN SILICON
350 VOLTS, 20 WATTS





TO−225
CASE 77−09
STYLE 1

MARKING DIAGRAM



Y = Year
WW = Work Week
BD159 = Device Code
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
BD159G	TO−225 (Pb−Free)	500 Units/Box

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Sustaining Voltage (I_C = 1.0 mAdc, I_B = 0)	BV_{CEO}	350	–	Vdc
Collector Cutoff Current (at rated voltage)	I_{CBO}	–	100	μAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)	I_{EBO}	–	100	μAdc
ON CHARACTERISTICS				
DC Current Gain (I_C = 50 mAdc, V_{CE} = 10 Vdc)	h_{FE}	30	240	–

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

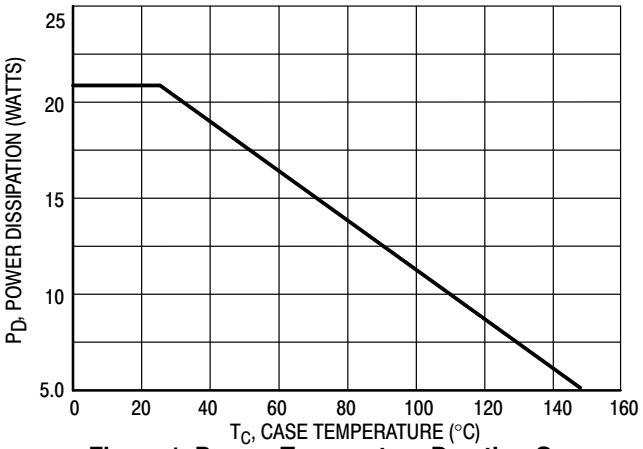


Figure 1. Power−Temperature Derating Curve

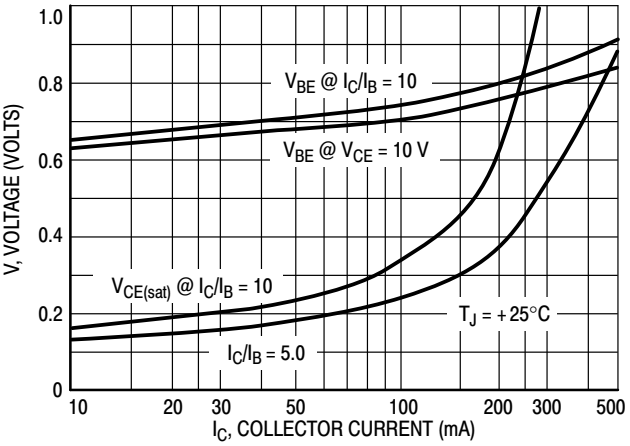


Figure 2. "On" Voltages

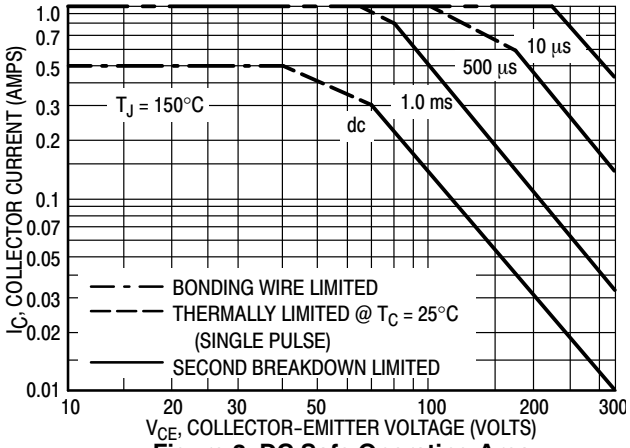


Figure 3. DC Safe Operating Area

The Safe Operating Area Curves indicate $I_C - V_{CE}$ limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below, the maximum T_J, power−temperature derating must be observed for both steady state and pulse power conditions.

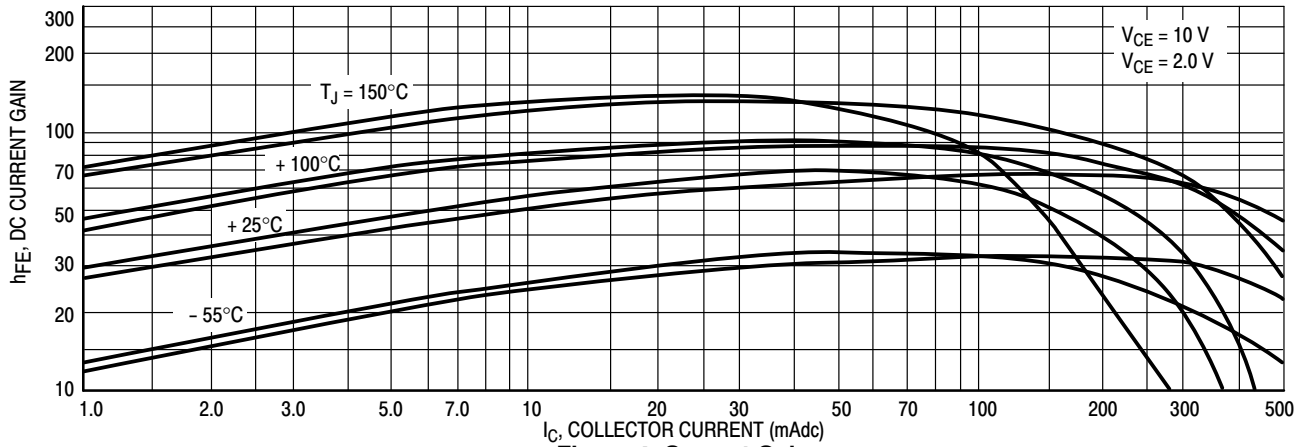
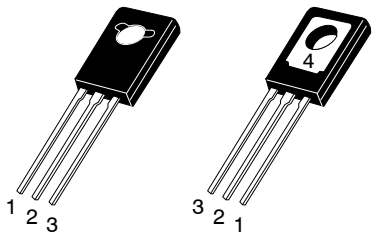


Figure 4. Current Gain

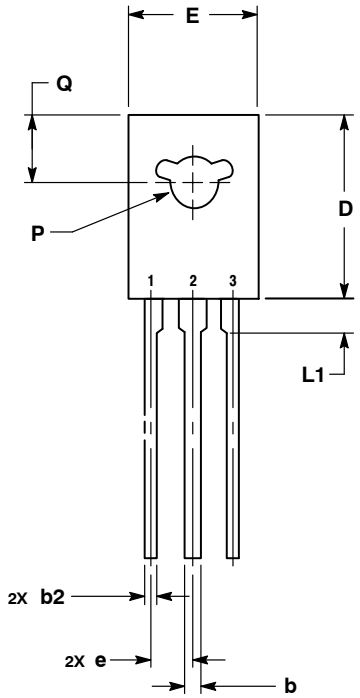


FRONT VIEW **BACK VIEW**

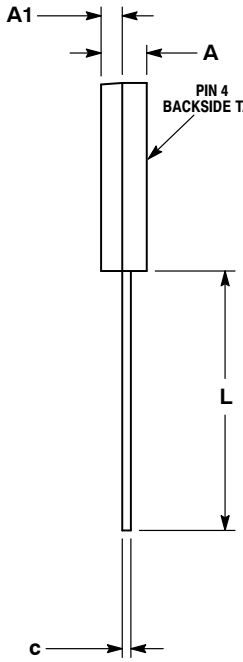
TO−225
CASE 77−09
ISSUE AD

DATE 25 MAR 2015

SCALE 1:1



FRONT VIEW

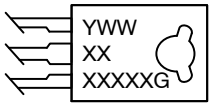


SIDE VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS	
DIM	MIN	MAX
A	2.40	3.00
A1	1.00	1.50
b	0.60	0.90
b2	0.51	0.88
c	0.39	0.63
D	10.60	11.10
E	7.40	7.80
e	2.04	2.54
L	14.50	16.63
L1	1.27	2.54
P	2.90	3.30
Q	3.80	4.20

GENERIC MARKING DIAGRAM*



Y = Year
WW = Work Week
XXXXX = Device Code
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. EMITTER
2., 4. COLLECTOR
3. BASE

STYLE 2:
PIN 1. CATHODE
2., 4. ANODE
3. GATE

STYLE 3:
PIN 1. BASE
2., 4. COLLECTOR
3. EMITTER

STYLE 4:
PIN 1. ANODE 1
2., 4. ANODE 2
3. GATE

STYLE 5:
PIN 1. MT 1
2., 4. MT 2
3. GATE

STYLE 6:
PIN 1. CATHODE
2., 4. GATE
3. ANODE

STYLE 7:
PIN 1. MT 1
2., 4. GATE
3. MT 2

STYLE 8:
PIN 1. SOURCE
2., 4. GATE
3. DRAIN

STYLE 9:
PIN 1. GATE
2., 4. DRAIN
3. SOURCE

STYLE 10:
PIN 1. SOURCE
2., 4. DRAIN
3. GATE

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